EE 330 Coverage - Fall 2007

		Topics
Week	1	
		1 Electronic Systems Overview, Economic Opportunities
		2 Viold and Cost of Somioonductor Droducto
		3 Physical characteristics, soft faults
Week	2	
		4 Digital Systems - Basic Gates, Switch-Level MOS Models
		5 Digital Systems - Complex Logic Gates, Pass Transistor Logic, Improved Switch-Level MOS Model
		6 Paramater Extraction for Imp. Switch-I evel Model, Propagation Delay in Logic, Placement, Stick Diagrams
Week	2	
week	3	
		Holiday
		7 Technology Files, Design Rules, Layout
		8 Fabrication Technology, Processing Steps
Week	4	
		9 Fabrication Technology, Processing Steps
		10 Interconnects - residue and canacitive
		14 Declarity - Lesistive and capacitive
	_	11 Backed Technology - Packaging, Bonding, Basic Semiconductor Processes
Week	5	
		12 Devices/Device Models in Semiconductor Proceses - Resistors, Diodes
		13 Diode Operation, Diode Model (Diode Equation), simplified diode models
		14 Diode Applications, Capacitor types and Models, MOSEET operation
Week	6	
WCCK	0	15 MOSEET Operation square low model short channel model RSIM model (brief)
		13 MOSFET Operation - square law model, short channel model, BSIM model (bher)
		16 MOS Process Description - (n-channel, p-channel, capacitors, resistors)
		17 Exam 1
Week	7	
		18 Small feature MOS processes, Bipolar Devices and operation
		19 Bipolar Devices - operation, device model, simplified device model
		20 Bipolar Process Description - (vertical and lateral devices IEET diffused resistor varactor diode)
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week	0	
		21 MOS and Bipolar Device Comparisons, Q-point calculation
		22 Transistors as Amplifiers (MOS and Bipolar)
		23 Small-signal principles, ss models of 2-terminal devices, ss diode model
Week	9	
		24 Small-signal models of 3-terminal and 4-terminal devices small signal MOSEET model
		25 Small-signal B IT models small signal ciruit analysis load lines signal swings
		20 Maar signal bei model Evidencien (Dully brackeld). Comparison of Mos and Bischer devices t
		26 MOSFET Model Extension (Buik Intreshold), Comparison of MOS and Bipolar devices t
		as amplifiers, Dependence of SS paramaters on Q-poin
Week	10	
		27 Basic Amplifier Structures-CS/CE, CD/CC, CG/CB
		28 Basic Amplifier Structures-CS/CE, CD/CC, CG/CB
		29 High Gain Amplifies- Cascoding
Wook	11	
WEEK		20 Link Onio Amelification Operation
		30 High Gain Amplifiers - Cascoding, Cascading
		31 Current Source Biasing, Darlington Configuration
		32 Current Sources and Mirrors
Week	12	
		33 Differential Amplifiers (brief), Bipolar and MOS Mappings
		34 Heirarchiada Digital Design - Rehavioral Structural Physical Digital Design Flows
		25 Provide Cates Characteristics of Logic Emilian the Inverter Dair
14/101	40	so basic Gales, Charactistics of Logic Families, the inverter Fam
VVeek	13	
		36 Analyysis of Logic Circuits (at transistor level), VH, VL, VTRIP,
		Static I/V Char of CMOS Inverter, Inverter Device Sizing
		37 Other CMOS Logic (ration logic), Propagation Delay in Static CMOS,
		Logic Gate Device Sizing, Reference Inverters
		38 Propagation Delay in Multiple Levels of Logic Overdrive
Mook	11	contropagation boldy in Midliple Lovels of Logic, Overlande
week	14	
		39 Asymmetric Overdrive and Propagation Delay, Driving large capacitive loade
		40 Pad Drivers, Logical Effort, Elmore Delay, Ring Oscillators
		41 Exam 2
Week	15	
		42 Complex Logic Gates, Pass Transistor Logic, Pseudo NMOS, Dvnamic Logic (Domino and Zipper)
		43 Sequential Logic - Latches Flip Flops Shift Registers Array Logic Sea of Gates and Gate Arrays
		Ad Mamony Structures - Row/Colum Decoders Mam Colls (SDAM DDAM SDOM EEDOM)
		High Eraguant MOS Madal (not appoint time to asuar)
		nigh Frequency MOS Model (not enough time to cover)